# **MMBV3401LT1G**

# **Silicon Pin Diode**

This device is designed primarily for VHF band switching applications but is also suitable for use in general-purpose switching circuits. Supplied in a Surface Mount package.

### **Features**

- Rugged PIN Structure Coupled with Wirebond Construction for Optimum Reliability
- Low Capacitance 0.7 pF (Typ) at  $V_R = 20 \text{ Vdc}$
- Very Low Series Resistance at 100 MHz
   0.34 Ω (Typ) @ I<sub>F</sub> = 10 mAdc
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	35	Vdc
Forward Power Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	200 2.0	mW mW/°C
Junction Temperature	TJ	+125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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SOT-23 (TO-236AB) CASE 318-08 STYLE 8

## **MARKING DIAGRAM**



4D = Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBV3401LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBV3401LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MMBV3401LT1G

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu Adc$ )	V <sub>(BR)R</sub>	35	-	-	Vdc
Diode Capacitance (V <sub>R</sub> = 20 Vdc)	C <sub>T</sub>	-	-	1.0	pF
Series Resistance (Figure 1) (I <sub>F</sub> = 10 mAdc, f = 100 MHz)	R <sub>S</sub>	-	-	0.7	Ω
Reverse Leakage Current (V <sub>R</sub> = 25 Vdc)	I <sub>R</sub>	-	-	0.1	μAdc

## TYPICAL CHARACTERISTICS

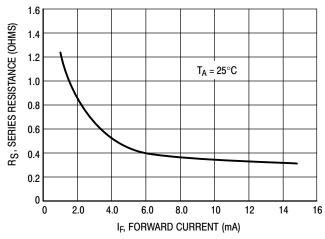


Figure 1. Series Resistance

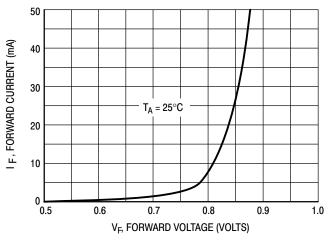
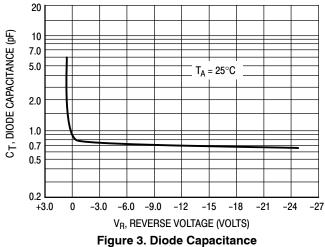


Figure 2. Forward Voltage



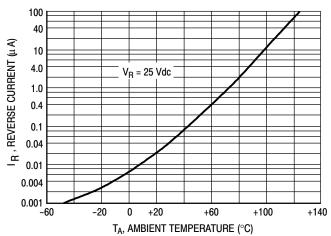


Figure 4. Leakage Current

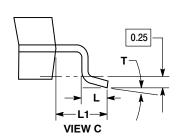


SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

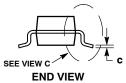
**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







## **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	5. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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